Supporting Information

Construction of Bi_2O_2Se/Bi_2Se_3 Van Der Waals Heterostructure for Self-powered and Broadband Photodetector

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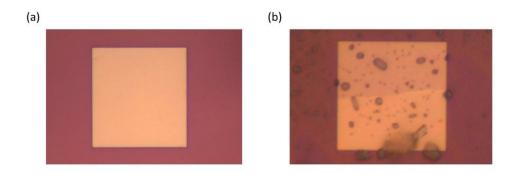


Figure S-1. The optical image of the transferred sample with (a) and without (b) small molecules naphthalene.

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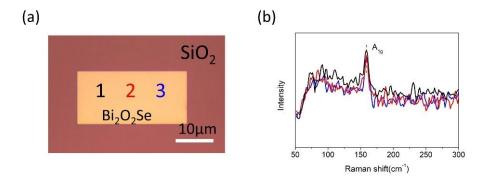


Figure S-2. (a) Optical image of samples transferred to a silicon substrate using the improved method. (b) The Raman characterization of different areas at the sample transferred to silicon substrate.

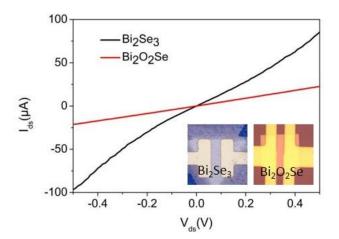


Figure S-3. The I-V characterizations of the individual Bi₂O₂Se and Bi₂Se₃ nanosheets. Inset: Optical images of corresponding devices.

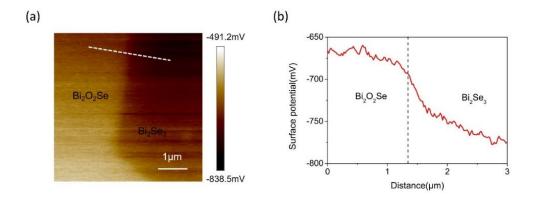


Figure S-4. (a) KPFM surface potential map of the heterostructure region (b) The surface potential profile across the sample corresponding to the dashed line in panel.

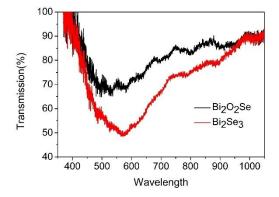


Figure S-5. The transmission characterization of the individual Bi_2O_2Se and Bi_2Se_3 nanosheets.

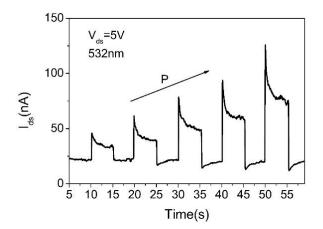


Figure S-6. Photoresponse of the heterostructure under different laser power (532 nm) at $V_{ds} = 5 \text{ V}$.

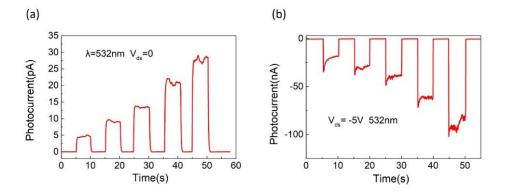


Figure S-7. I-T response curves of the heterostructure device at 0V (a) and -5V (b).